

Cool MOS™ Power Transistor



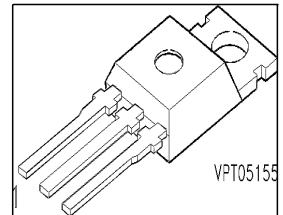
Feature

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved noise immunity

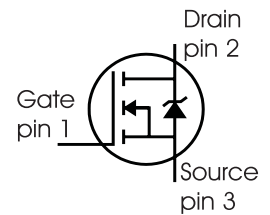
Product Summary

V_{DS}	800	V
$R_{DS(on)}$	900	mΩ
I_D	6	A

P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP06N80C2	P-TO220-3-1	Q67040-S4351	SPP06N80C2



Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$	I_D	6 3.8	A
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\text{ puls}}$	18	
Avalanche energy, single pulse $I_D=1.5\text{A}, V_{DD}=50\text{V}$	E_{AS}	230	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹⁾ $I_D=6\text{A}, V_{DD}=50\text{V}$	E_{AR}	0.2	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	6	A
Reverse diode dv/dt $I_S=6\text{A}, V_{DS} < V_{DD}, di/dt=100\text{A}/\mu\text{s}, T_{jmax}=150\text{°C}$	dv/dt	6	V/ns
Gate source voltage	V_{GS}	±20	V
Power dissipation $T_C = 25\text{ °C}$	P_{tot}	83	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Linear derating factor		-	-	0.67	W/K
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Static Characteristics

Drain-source breakdown voltage $V_{GS}=0V, I_D=0.25mA$	$V_{(BR)DSS}$	800	-	-	V
Drain-source avalanche breakdown voltage $V_{GS}=0V, I_D=6A$	$V_{(BR)DS}$	-	870	-	
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=250\mu A$	$V_{GS(th)}$	2	3	4	
Zero gate voltage drain current $V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}, T_j = 150\text{ °C}$	I_{DSS}	-	0.5	10	μA
		-	-	100	
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	-	100	nA
Drain-source on-state resistance $V_{GS}=10V, I_D=3.8A, T_j=25\text{ °C}$	$R_{DS(on)}$	-	780	900	m Ω
Gate input resistance $f = 1\text{ MHz}$, open drain	R_G	-	0.7	-	Ω

¹Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

Electrical Characteristics , at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 3.8\text{A}$	-	4	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$,	-	785	-	pF
Output capacitance	C_{oss}	$f = 1\text{MHz}$	-	390	-	
Reverse transfer capacitance	C_{rss}		-	20	-	
Effective output capacitance, ¹⁾ energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 640\text{V}$	-	22	-	pF
Effective output capacitance, ²⁾ time related	$C_{o(tr)}$		-	42	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{V}$, $V_{GS} = 0/10\text{V}$,	-	25	-	ns
Rise time	t_r	$I_D = 6\text{A}$, $R_G = 12\Omega$,	-	15	-	
Turn-off delay time	$t_{d(off)}$	$T_f = 125^\circ\text{C}$	-	48	60	
Fall time	t_f		-	8	13	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 640\text{V}$, $I_D = 6\text{A}$	-	2.5	-	nC
Gate to drain charge	Q_{gd}		-	9.8	-	
Gate charge total	Q_g	$V_{DD} = 640\text{V}$, $I_D = 6\text{A}$, $V_{GS} = 0\text{ to } 10\text{V}$	-	19.4	25	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 640\text{V}$, $I_D = 6\text{A}$	-	6	-	V

¹ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

² $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

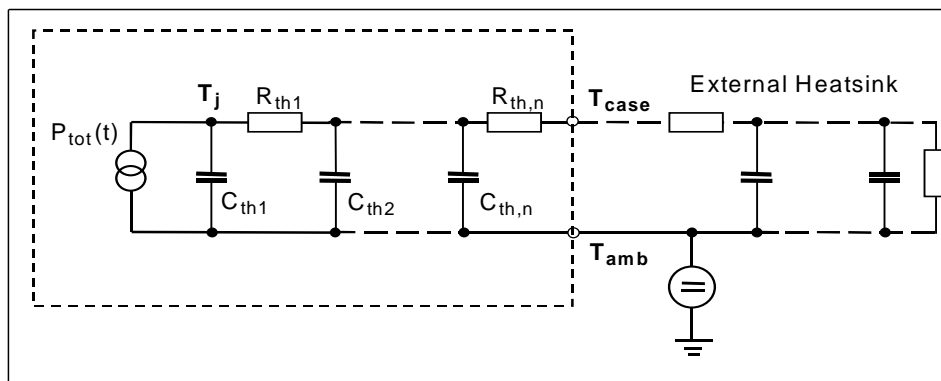
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Reverse Diode						
Inverse diode continuous forward current	I_S	$T_C=25^\circ\text{C}$	-	-	6	A
Inverse diode direct current, pulsed	I_{SM}		-	-	18	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=400\text{V}, I_F=I_S,$	-	520	-	ns
Reverse recovery charge	Q_{rr}	$di_F/dt=100\text{A}/\mu\text{s}$	-	5	-	μC
Peak reverse recovery current	I_{rrm}		-	17	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	400	-	$\text{A}/\mu\text{s}$

Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	

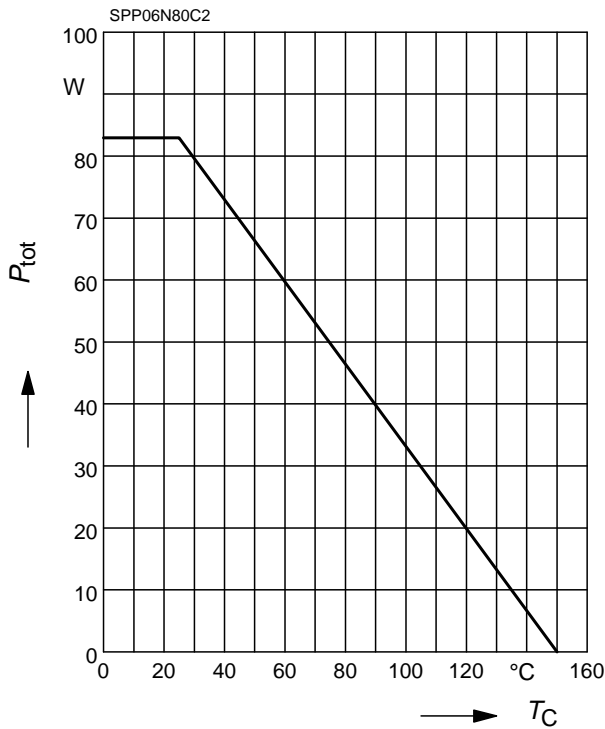
Transient thermal impedance

Thermal resistance			Thermal capacitance		
R_{th1}	0.023	K/W	C_{th1}	0.000135	Ws/K
R_{th2}	0.033		C_{th2}	0.000438	
R_{th3}	0.067		C_{th3}	0.000313	
R_{th4}	0.189		C_{th4}	0.00149	
R_{th5}	0.208		C_{th5}	0.00738	
R_{th6}	0.076		C_{th6}	0.068	



1 Power dissipation

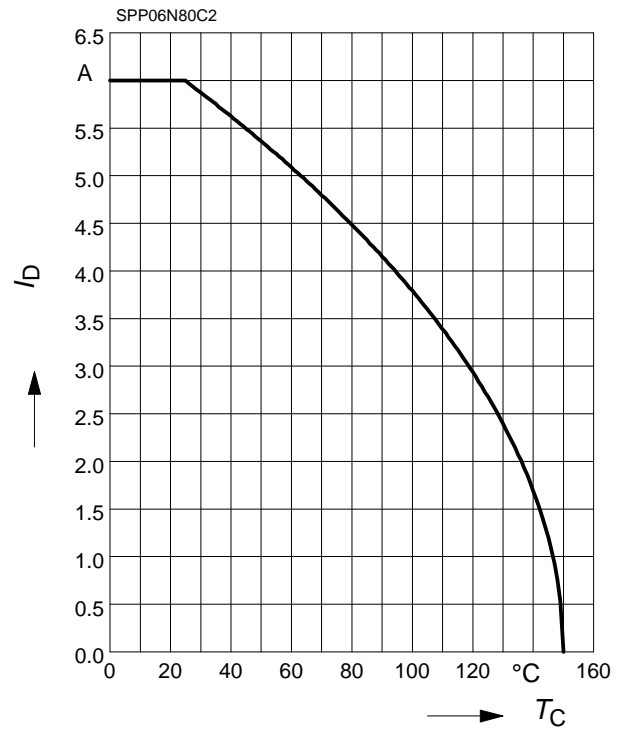
$$P_{\text{tot}} = f(T_C)$$



2 Drain current

$$I_D = f(T_C)$$

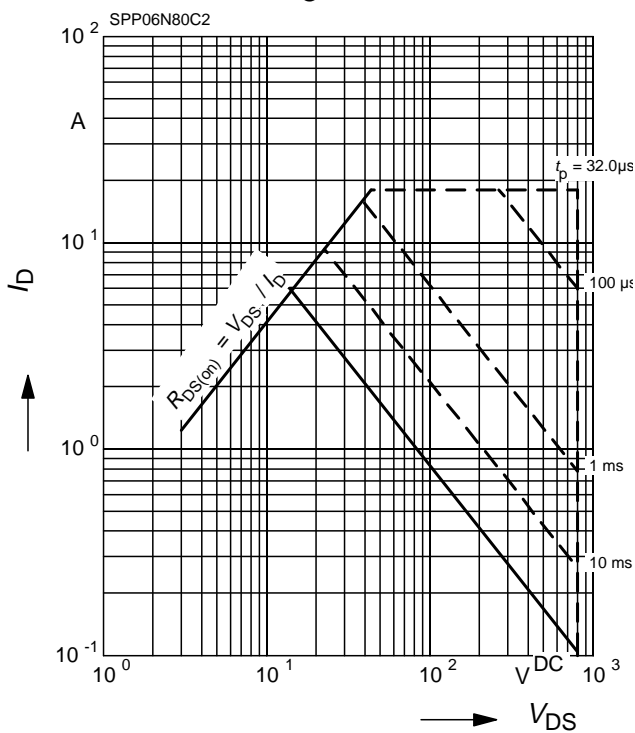
parameter: $V_{GS} \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

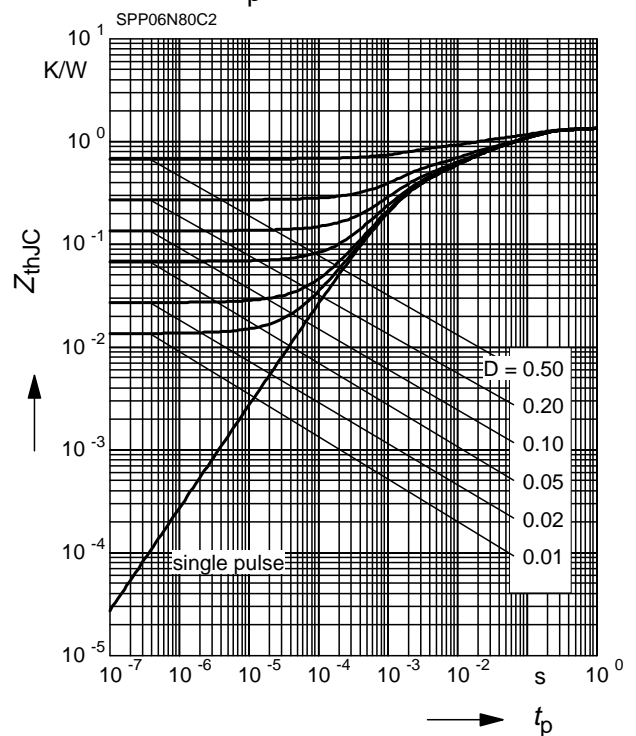
parameter: $D = 0$, $T_C = 25^\circ\text{C}$



4 Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

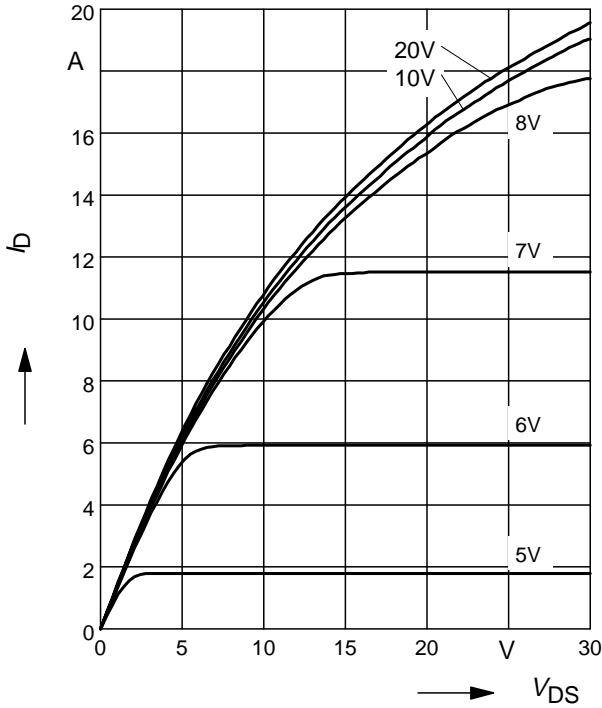
parameter: $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

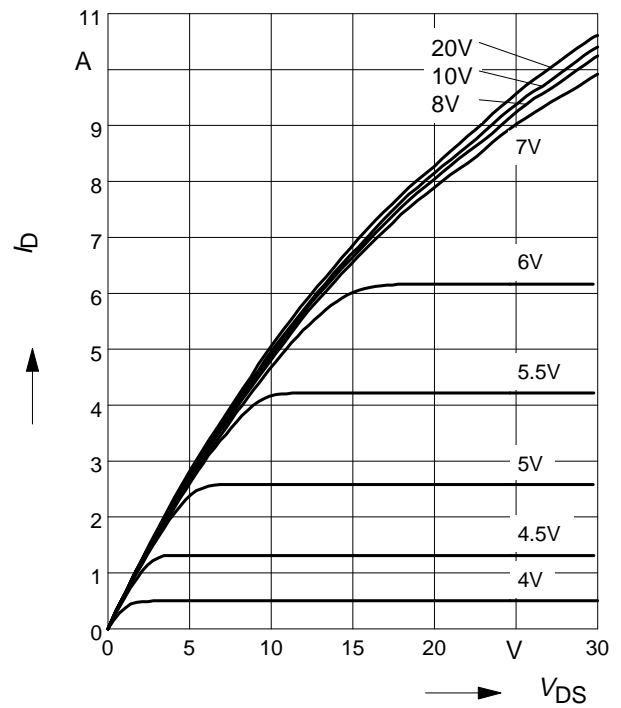
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



6 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

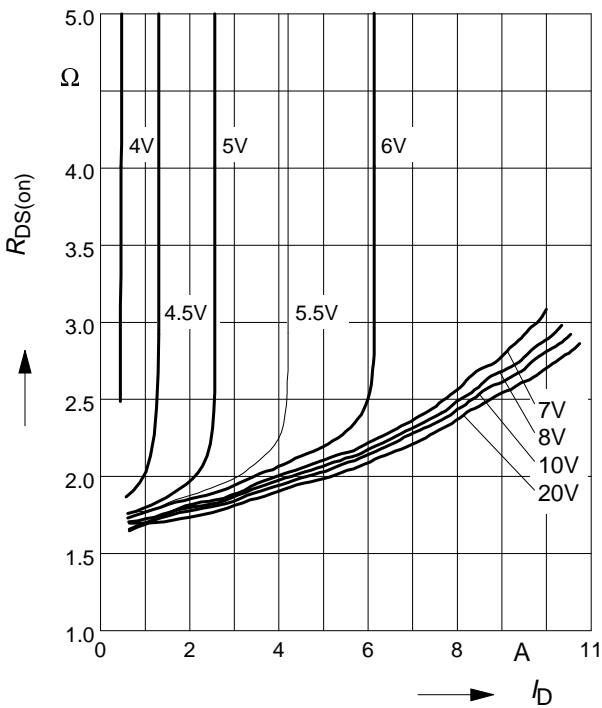
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



7 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

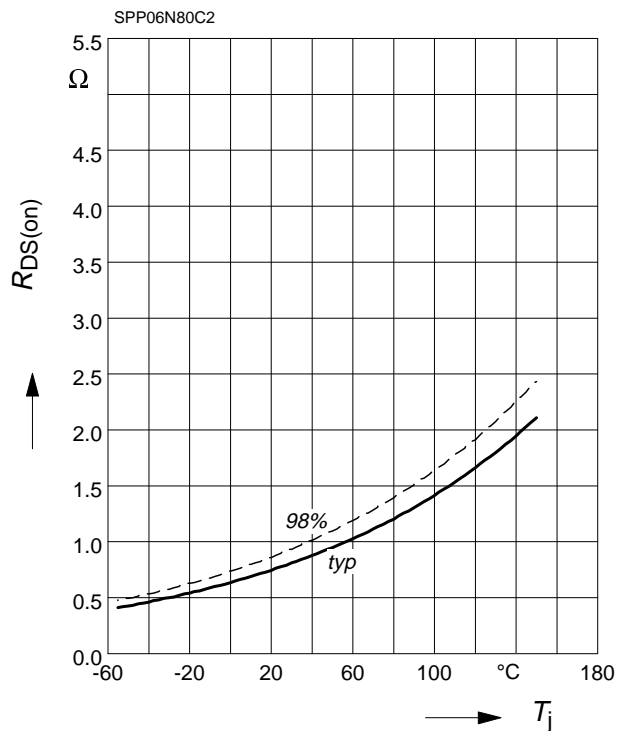
parameter: $T_j = 150^\circ\text{C}, V_{GS}$



8 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

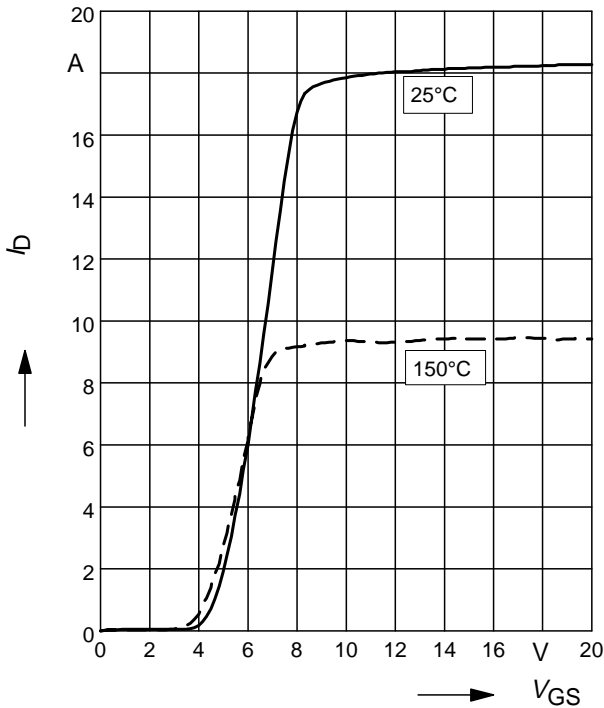
parameter: $I_D = 3.8 \text{ A}, V_{GS} = 10 \text{ V}$



9 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

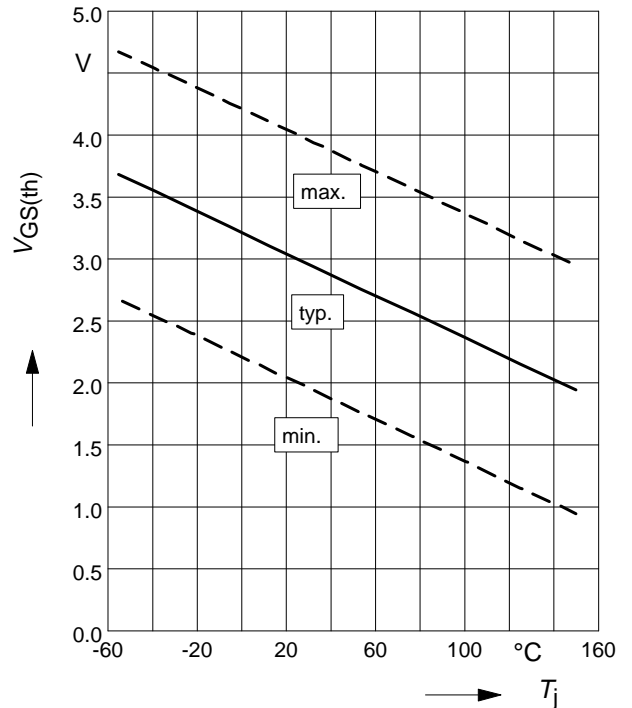
parameter: $t_p = 10 \mu s$



10 Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

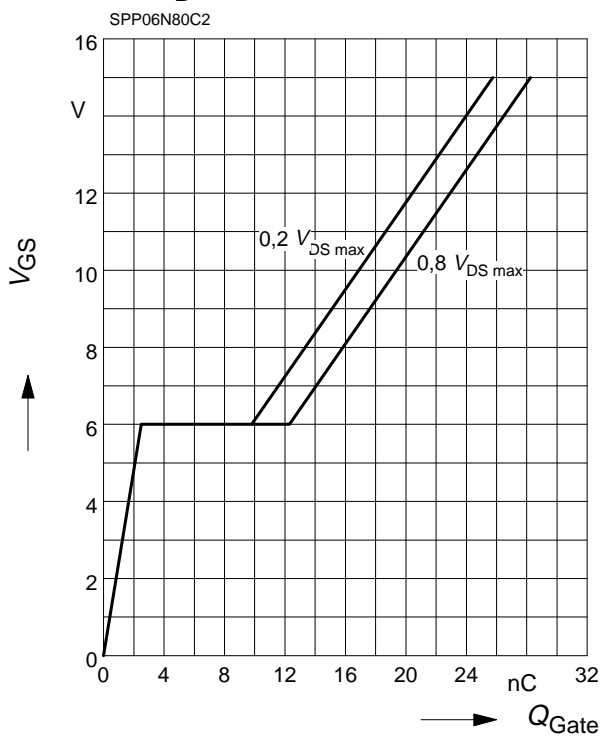
parameter: $V_{GS} = V_{DS}, I_D = 250 \mu A$



11 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

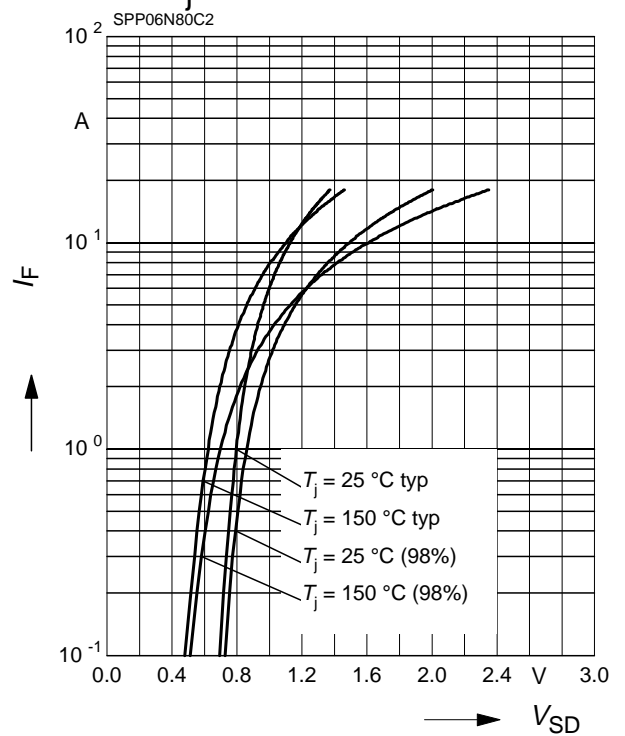
parameter: $I_D = 6 A$ pulsed



12 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

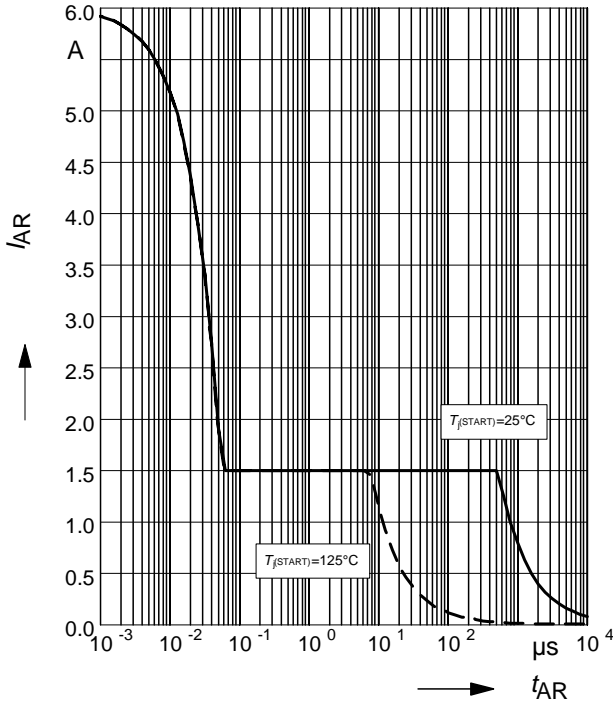
parameter: $T_j, t_p = 10 \mu s$



13 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

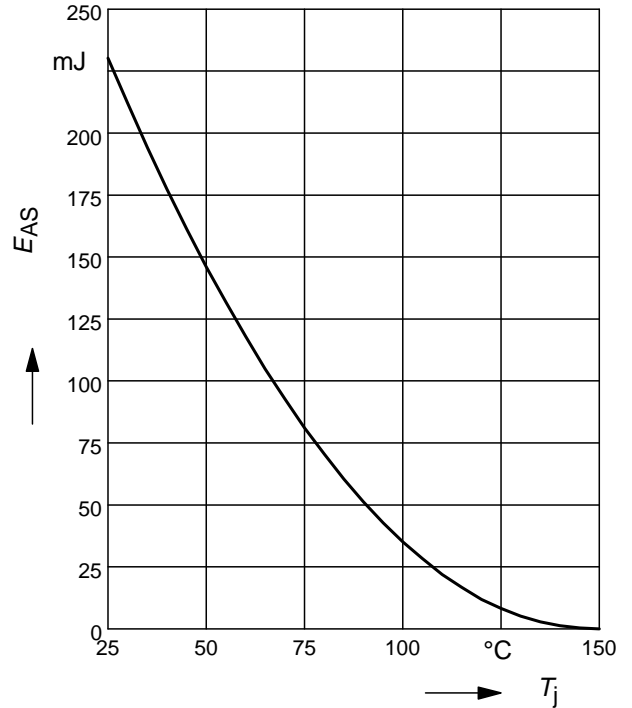
par.: $T_j \leq 150\text{ }^\circ\text{C}$



14 Avalanche energy

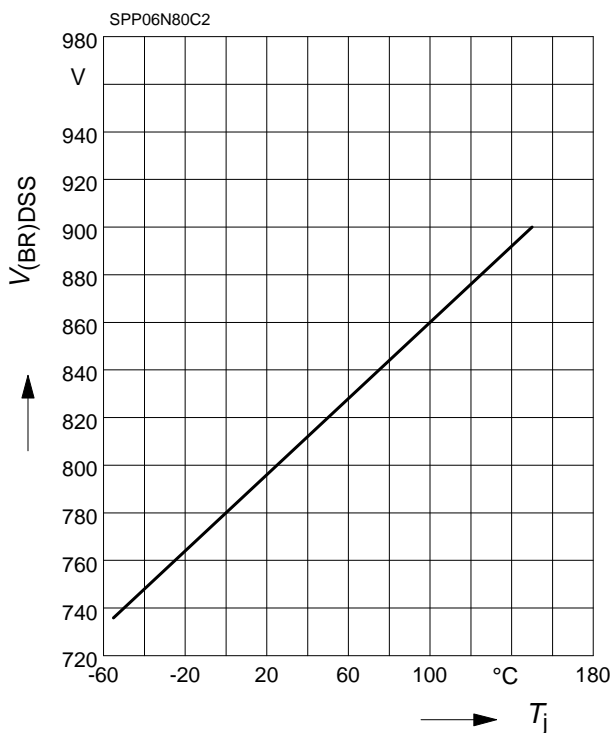
$$E_{AS} = f(T_j)$$

par.: $I_D = 1.5\text{ A}$, $V_{DD} = 50\text{ V}$



15 Drain-source breakdown voltage

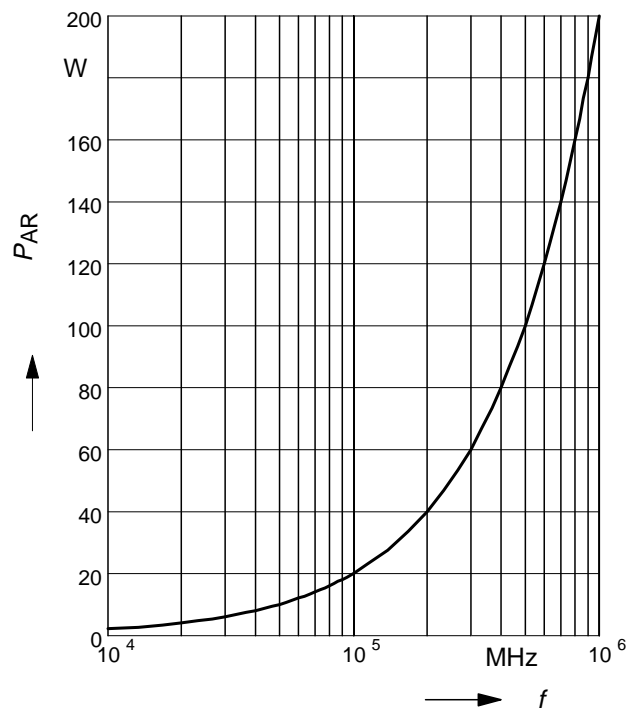
$$V_{(BR)DSS} = f(T_j)$$



16 Avalanche power losses

$$P_{AR} = f(f)$$

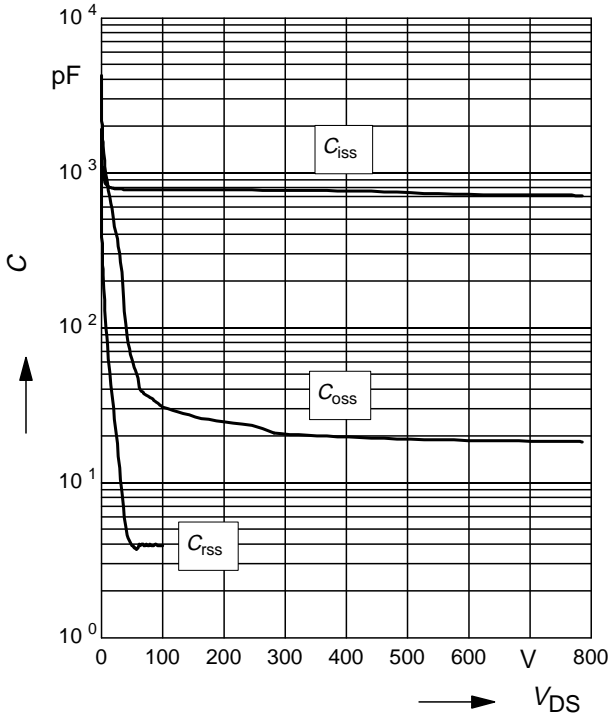
parameter: $E_{AR} = 0.2\text{ mJ}$



17 Typ. capacitances

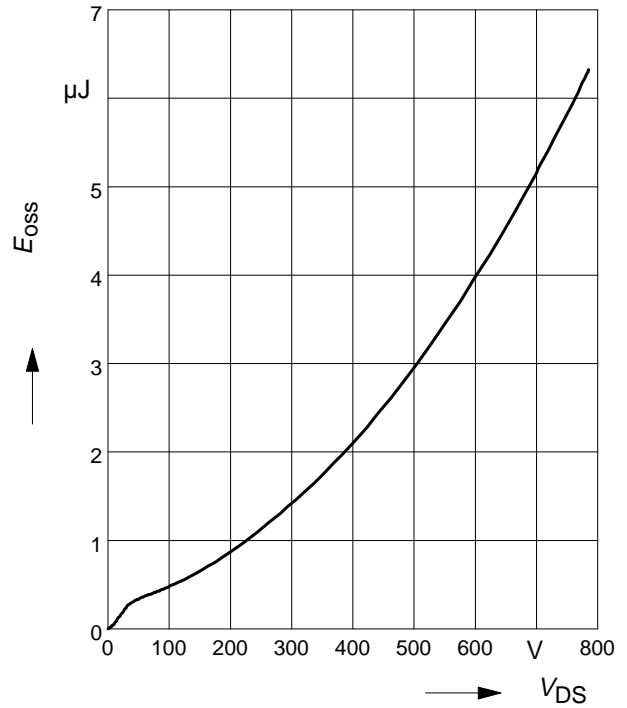
$$C = f(V_{DS})$$

parameter: $V_{GS}=0V, f=1\text{ MHz}$

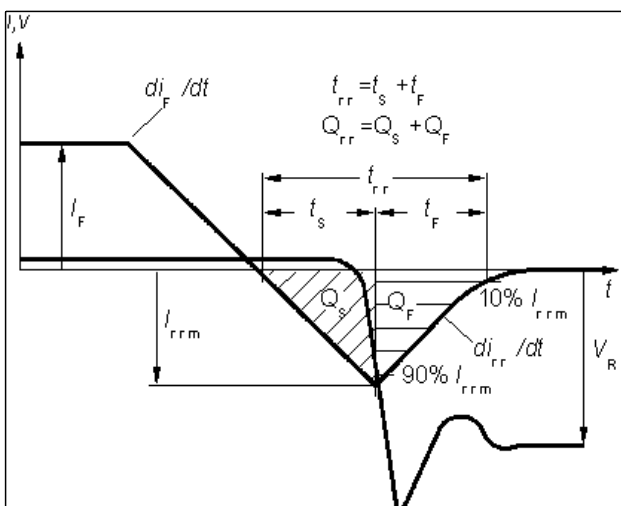


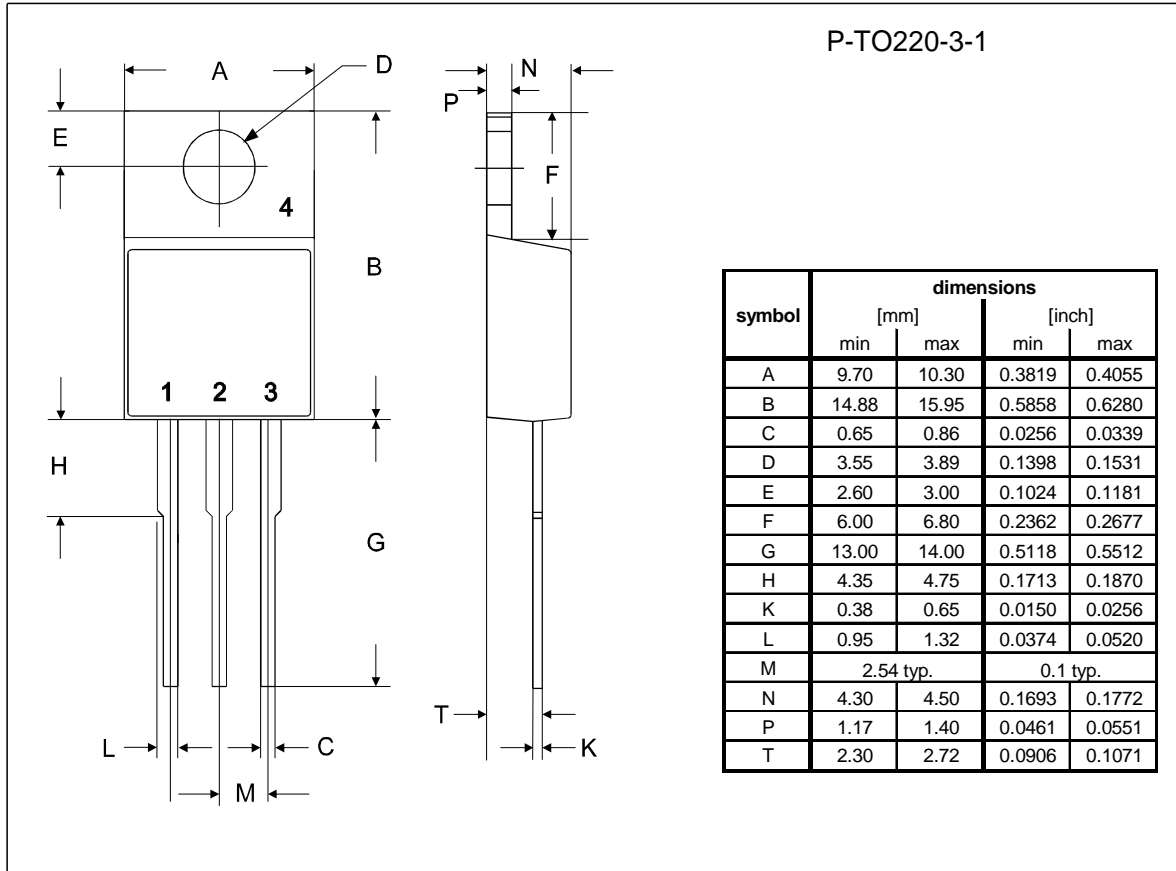
18 Typ. C_{oss} stored energy

$$E_{oss} = f(V_{DS})$$



Definition of diodes switching characteristics





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